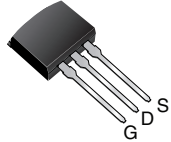
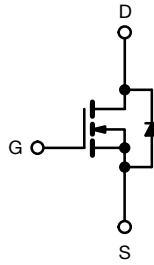
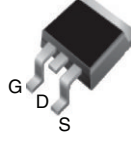


## Power MOSFET

 I<sup>2</sup>PAK (TO-262)

 D<sup>2</sup>PAK (TO-261)


N-Channel MOSFET

### FEATURES

- Dynamic dV/dt rating
- Repetitive avalanche rated
- Fast switching
- Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



RoHS\*  
Available  
HALOGEN  
FREE  
Available

### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

### DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

### PRODUCT SUMMARY

|                          |                        |     |
|--------------------------|------------------------|-----|
| V <sub>DS</sub> (V)      | 800                    |     |
| R <sub>DS(on)</sub> (Ω)  | V <sub>GS</sub> = 10 V | 3.0 |
| Q <sub>g</sub> max. (nC) | 78                     |     |
| Q <sub>gs</sub> (nC)     | 9.6                    |     |
| Q <sub>gd</sub> (nC)     | 45                     |     |
| Configuration            | Single                 |     |

### ORDERING INFORMATION

|                                 |                             |                               |                             |
|---------------------------------|-----------------------------|-------------------------------|-----------------------------|
| Package                         | D <sup>2</sup> PAK (TO-263) | D <sup>2</sup> PAK (TO-263)   | I <sup>2</sup> PAK (TO-262) |
| Lead (Pb)-free and Halogen-free | SiHFBE30S-GE3               | SiHFBE30STRL-GE3 <sup>a</sup> | SiHFBE30L-GE3               |
| Lead (Pb)-free                  | IRFBE30SPbF                 | IRFBE30STRLPbF <sup>a</sup>   | IRFBE30LPbF                 |

### Note

a. See device orientation

### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25 °C, unless otherwise noted)

| PARAMETER   | SYMBOL                            | LIMIT                   | UNIT |          |
|---|-----------------------------------|-------------------------|------|----------|
| Drain-Source Voltage                                      | V <sub>DS</sub>                   | 800                     | V    |          |
| Gate-Source Voltage                                       | V <sub>GS</sub>                   | ± 20                    |      |          |
| Continuous Drain Current                                  | I <sub>D</sub>                    | T <sub>C</sub> = 25 °C  | A    |          |
|   |                                   | T <sub>C</sub> = 100 °C |      | 4.1      |
| Pulsed Drain Current <sup>a</sup>                         | I <sub>DM</sub>                   | 16                      | W/°C |          |
| Linear Derating Factor                                    |                                   | 1.0                     |      |          |
| Single Pulse Avalanche Energy <sup>b</sup>                | E <sub>AS</sub>                   | 260                     | mJ   |          |
| Avalanche Current <sup>a</sup>                            | I <sub>AR</sub>                   | 4.1                     | A    |          |
| Repetitive Avalanche Energy <sup>a</sup>                  | E <sub>AR</sub>                   | 13                      | mJ   |          |
| Maximum Power Dissipation                                 | P <sub>D</sub>                    | 125                     | W    |          |
| Peak Diode Recovery dV/dt <sup>c</sup>                    | dV/dt                             | 2.0                     | V/ns |          |
| Operating Junction and Storage Temperature Range          | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150             | °C   |          |
| Soldering Recommendations (Peak temperature) <sup>d</sup> | for 10 s                          | 300                     |      |          |
| Mounting Torque   | 6-32 or M3 screw                  |                         | 10   | lbf · in |
|   |                                   |                         | 1.1  | N · m    |

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- V<sub>DD</sub> = 50 V, starting T<sub>J</sub> = 25 °C, L = 29 mH, R<sub>g</sub> = 25 Ω, I<sub>AS</sub> = 4.1 A (see fig. 12)
- I<sub>SD</sub> ≤ 4.1 A, dI/dt ≤ 100 A/μs, V<sub>DD</sub> ≤ 600 V, T<sub>J</sub> ≤ 150 °C
- 1.6 mm from case

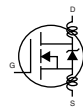
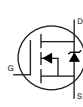


| THERMAL RESISTANCE RATINGS          |            |      |      |      |      |  |
|-------------------------------------|------------|------|------|------|------|--|
| PARAMETER                           | SYMBOL     | MIN. | TYP. | MAX. | UNIT |  |
| Maximum Junction-to-Ambient         | $R_{thJA}$ | -    | -    | 62   | °C/W |  |
| Case-to-Sink, Flat, Greased Surface | $R_{thCS}$ | -    | 0.50 | -    |      |  |
| Maximum Junction-to-Case (Drain)    | $R_{thJC}$ | -    | -    | 1.0  |      |  |

**Note**

a. When mounted on 1" square PCB (FR-4 or G-10 material)

**SPECIFICATIONS** ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)

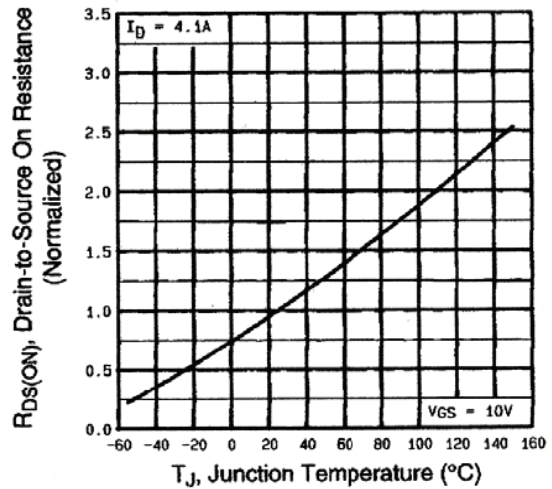
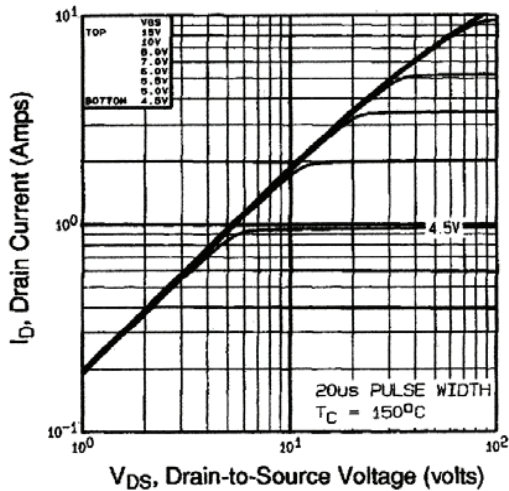
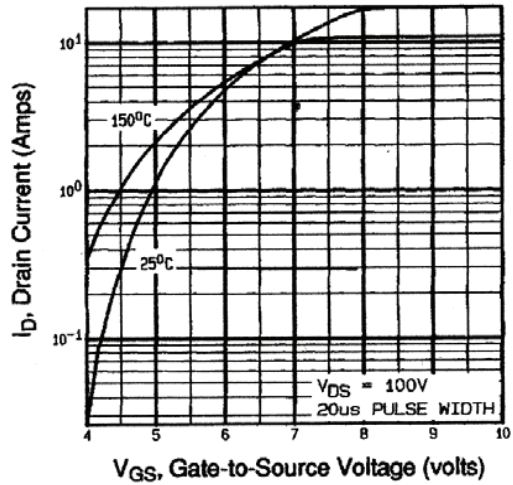
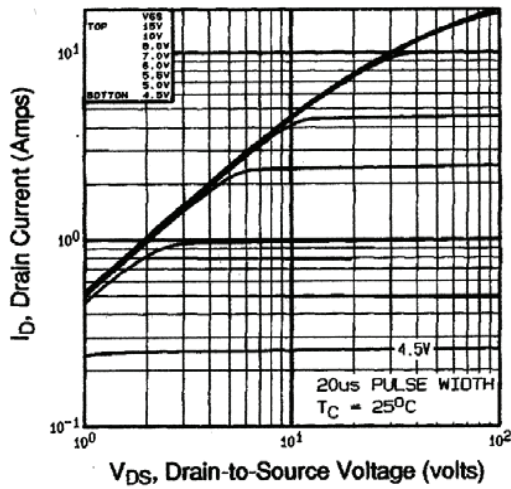
| PARAMETER                                      | SYMBOL              | TEST CONDITIONS   |  | MIN. | TYP. | MAX.      | UNIT          |
|--|---------------------|---|--|------|------|-----------|---------------|
| <b>Static</b>                                  |                     |   |  |      |      |           |               |
| Drain-Source Breakdown Voltage                 | $V_{DS}$            | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$   |  | 800  | -    | -         | V             |
| $V_{DS}$ Temperature Coefficient               | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$  |  | -    | 0.90 | -         | V/°C          |
| Gate-Source Threshold Voltage                  | $V_{GS(th)}$        | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$   |  | 2.0  | -    | 4.0       | V             |
| Gate-Source Leakage                            | $I_{GSS}$           | $V_{GS} = \pm 20\text{ V}$  |  | -    | -    | $\pm 100$ | nA            |
| Zero Gate Voltage Drain Current                | $I_{DSS}$           | $V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$  |  | -    | -    | 100       | $\mu\text{A}$ |
|  |                     | $V_{DS} = 640\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$   |  | -    | -    | 500       |               |
| Drain-Source On-State Resistance               | $R_{DS(on)}$        | $V_{GS} = 10\text{ V}$  | $I_D = 2.5\text{ A}^b$   | -    | -    | 3.0       | $\Omega$      |
| Forward Transconductance                       | $g_{fs}$            | $V_{DS} = 100\text{ V}, I_D = 2.5\text{ A}$   |  | 2.5  | -    | -         | S             |
| <b>Dynamic</b>                                 |                     |   |  |      |      |           |               |
| Input Capacitance                              | $C_{iss}$           | $V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}, \text{ see fig. 5}$   |  | -    | 1300 | -         | pF            |
| Output Capacitance                             | $C_{oss}$           |   |  | -    | 310  | -         |               |
| Reverse Transfer Capacitance                   | $C_{rss}$           |   |  | -    | 190  | -         |               |
| Total Gate Charge                              | $Q_g$               | $V_{GS} = 10\text{ V}$  | $I_D = 4.1\text{ A}, V_{DS} = 400\text{ V}, \text{ see fig. 6 and 13}^b$ | -    | -    | 78        | nC            |
| Gate-Source Charge                             | $Q_{gs}$            |   |  | -    | -    | 9.6       |               |
| Gate-Drain Charge                              | $Q_{gd}$            |   |  | -    | -    | 45        |               |
| Turn-On Delay Time                             | $t_{d(on)}$         | $V_{DD} = 400\text{ V}, I_D = 4.1\text{ A}, R_g = 12\text{ }\Omega, R_D = 95\text{ }\Omega, \text{ see fig. 10}^b$                                      |  | -    | 12   | -         | ns            |
| Rise Time                                      | $t_r$               |   |  | -    | 33   | -         |               |
| Turn-Off Delay Time                            | $t_{d(off)}$        |   |  | -    | 82   | -         |               |
| Fall Time                                      | $t_f$               |   |  | -    | 30   | -         |               |
| Gate Input Resistance                          | $R_g$               | $f = 1\text{ MHz}, \text{ open drain}$  |  | 0.6  | -    | 1.6       | $\Omega$      |
| Internal Drain Inductance                      | $L_D$               | Between lead, 6 mm (0.25") from package and center of die contact  |  | -    | 4.5  | -         | nH            |
| Internal Source Inductance                     | $L_S$               |   |  | -    | 7.5  | -         |               |
| <b>Drain-Source Body Diode Characteristics</b> |                     |   |  |      |      |           |               |
| Continuous Source-Drain Diode Current          | $I_S$               | MOSFET symbol showing the integral reverse p - n junction diode    |  | -    | -    | 4.1       | A             |
| Pulsed Diode Forward Current <sup>a</sup>      | $I_{SM}$            |   |  | -    | -    | 16        |               |
| Body Diode Voltage                             | $V_{SD}$            | $T_J = 25\text{ }^\circ\text{C}, I_S = 4.1\text{ A}, V_{GS} = 0\text{ V}^b$   |  | -    | -    | 1.8       | V             |
| Body Diode Reverse Recovery Time               | $t_{rr}$            | $T_J = 25\text{ }^\circ\text{C}, I_F = 4.1\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$  |  | -    | 480  | 720       | ns            |
| Body Diode Reverse Recovery Charge             | $Q_{rr}$            |   |  | -    | 1.8  | 2.7       |               |
| Forward Turn-On Time                           | $t_{on}$            | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )   |  |      |      |           |               |

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$



## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



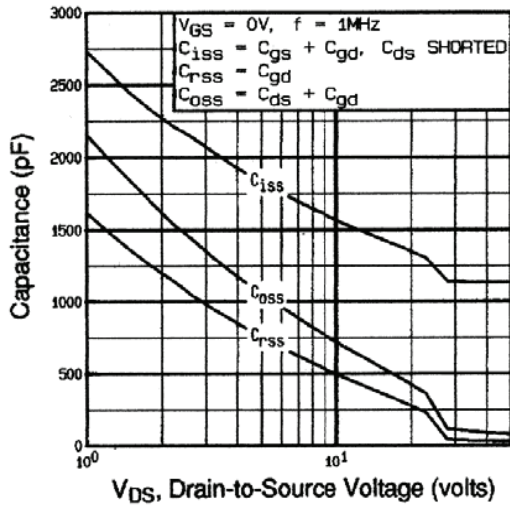


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

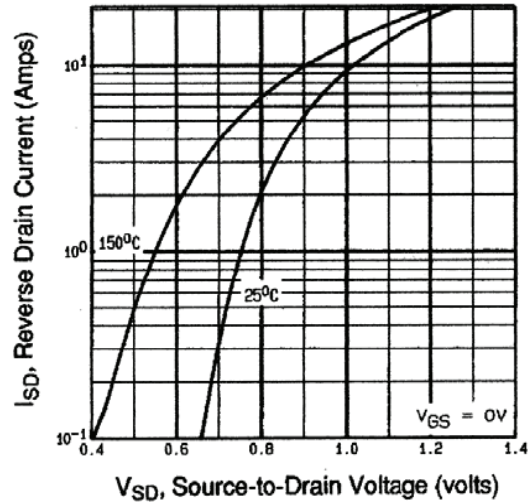


Fig. 7 - Typical Source-Drain Diode Forward Voltage

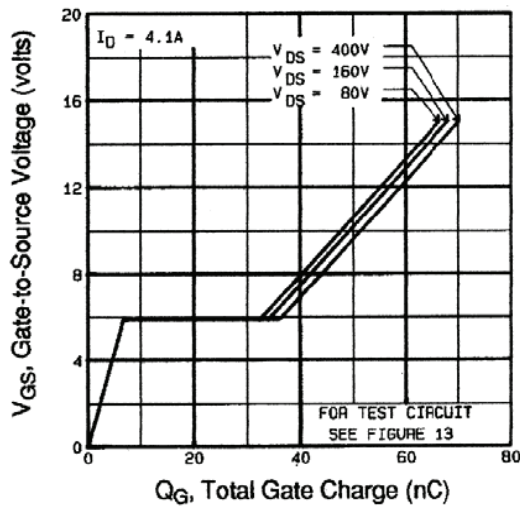


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

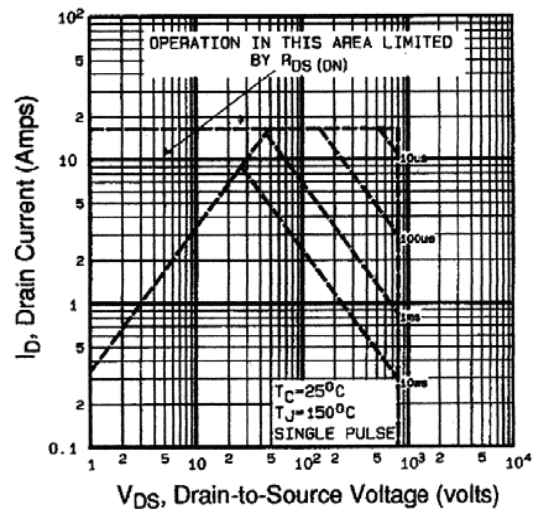


Fig. 8 - Maximum Safe Operating Area

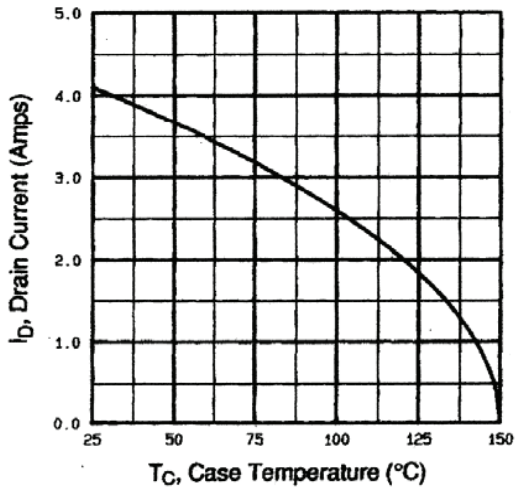


Fig. 9 - Maximum Drain Current vs. Case Temperature

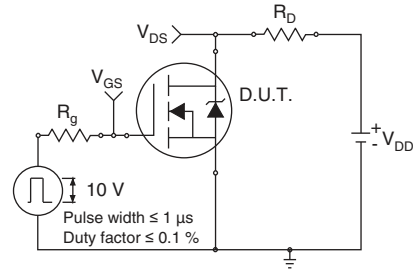


Fig. 10a - Switching Time Test Circuit

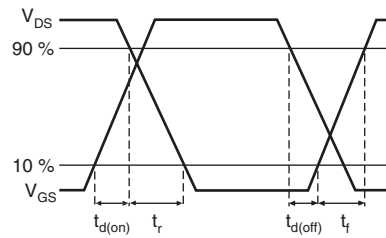


Fig. 10b - Switching Time Waveforms

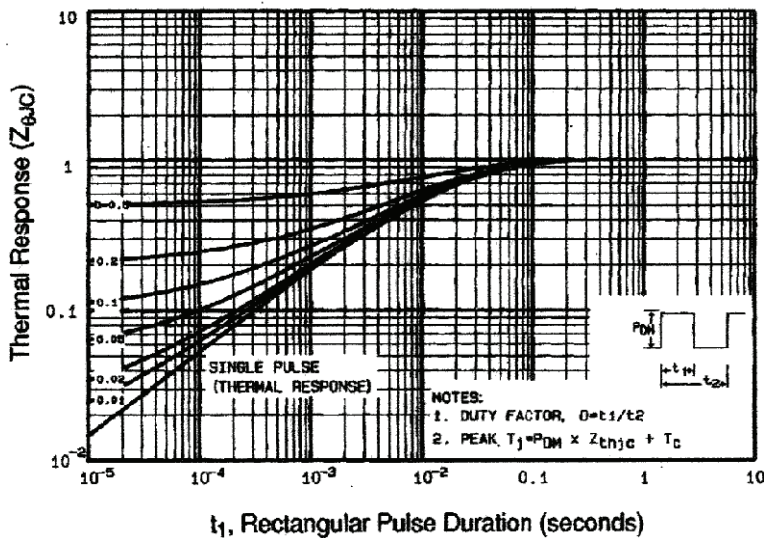


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

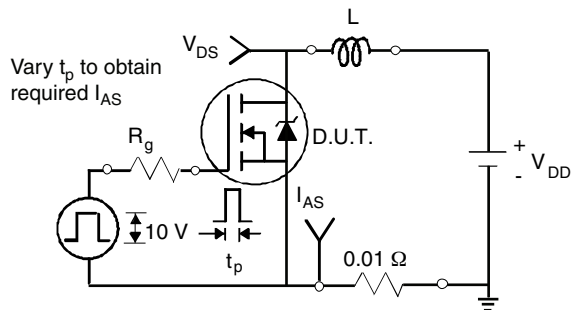


Fig. 12a - Unclamped Inductive Test Circuit

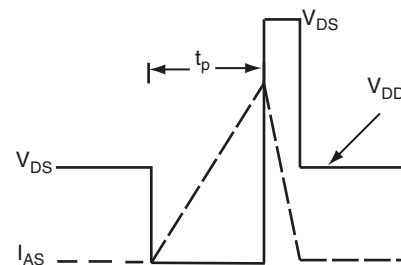


Fig. 12b - Unclamped Inductive Waveforms

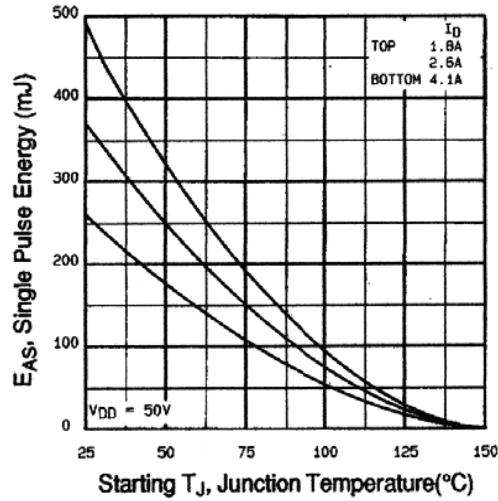


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

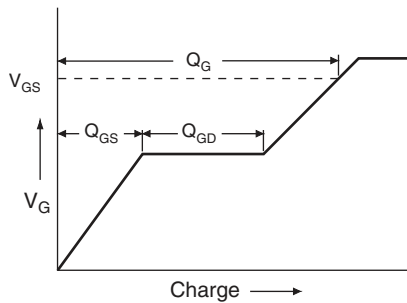


Fig. 13a - Maximum Avalanche Energy vs. Drain Current

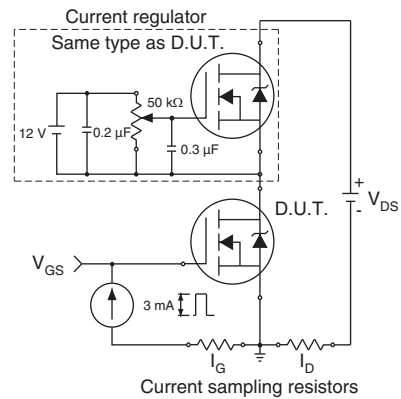
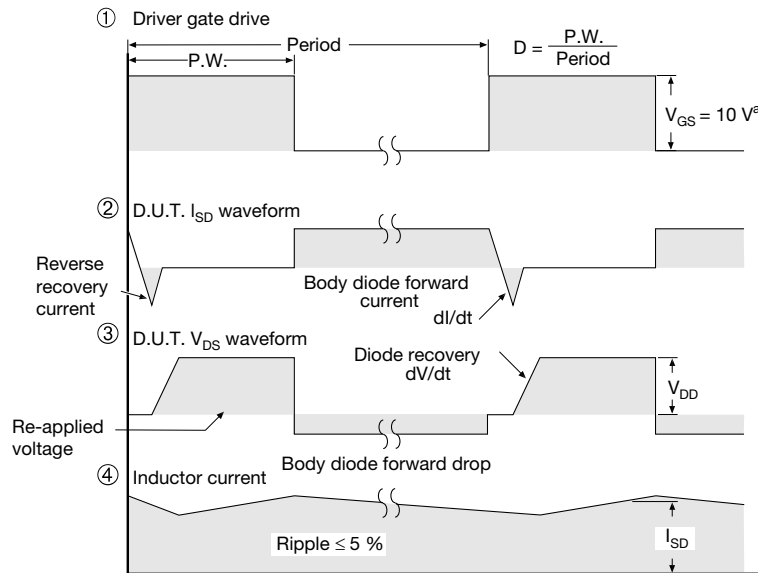
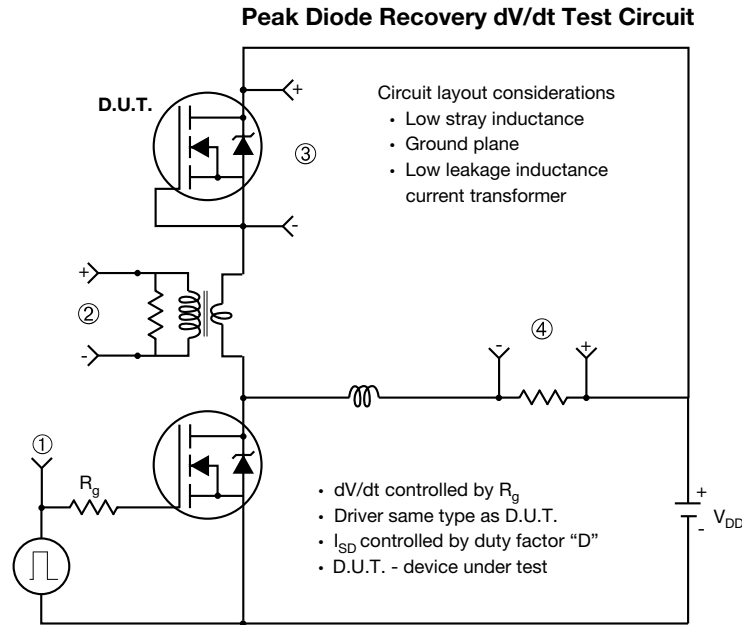


Fig. 13b - Gate Charge Test Circuit





**Note**

a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

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## I<sup>2</sup>PAK (TO-262) (HIGH VOLTAGE)



| DIM. | MILLIMETERS |      | INCHES |       |
|------|-------------|------|--------|-------|
|      | MIN.        | MAX. | MIN.   | MAX.  |
| A    | 4.06        | 4.83 | 0.160  | 0.190 |
| A1   | 2.03        | 3.02 | 0.080  | 0.119 |
| b    | 0.51        | 0.99 | 0.020  | 0.039 |
| b1   | 0.51        | 0.89 | 0.020  | 0.035 |
| b2   | 1.14        | 1.78 | 0.045  | 0.070 |
| b3   | 1.14        | 1.73 | 0.045  | 0.068 |
| c    | 0.38        | 0.74 | 0.015  | 0.029 |
| c1   | 0.38        | 0.58 | 0.015  | 0.023 |
| c2   | 1.14        | 1.65 | 0.045  | 0.065 |

| DIM. | MILLIMETERS |       | INCHES    |       |
|------|-------------|-------|-----------|-------|
|      | MIN.        | MAX.  | MIN.      | MAX.  |
| D    | 8.38        | 9.65  | 0.330     | 0.380 |
| D1   | 6.86        | -     | 0.270     | -     |
| E    | 9.65        | 10.67 | 0.380     | 0.420 |
| E1   | 6.22        | -     | 0.245     | -     |
| e    | 2.54 BSC    |       | 0.100 BSC |       |
| L    | 13.46       | 14.10 | 0.530     | 0.555 |
| L1   | -           | 1.65  | -         | 0.065 |
| L2   | 3.56        | 3.71  | 0.140     | 0.146 |

ECN: S-82442-Rev. A, 27-Oct-08  
DWG: 5977

### Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outmost extremes of the plastic body.
3. Thermal pad contour optional within dimension E, L1, D1, and E1.
4. Dimension b1 and c1 apply to base metal only.

**RECOMMENDED MINIMUM PADS FOR D<sup>2</sup>PAK: 3-Lead**



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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